

RESEARCH ARTICLE

Giant enhancement of photoluminescence emission in monolayer WS₂ by femtosecond laser irradiation

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Supplementary Materials

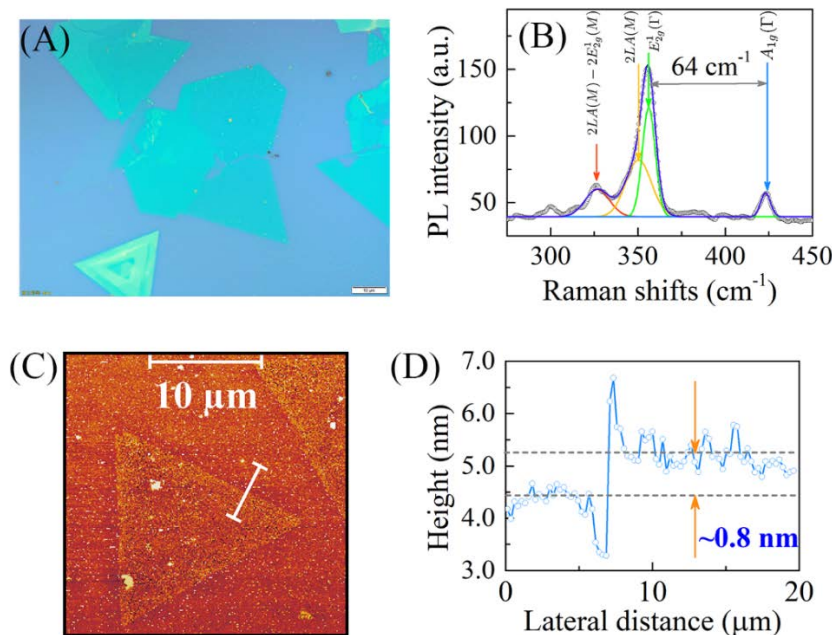


Fig. S1 Characterizations of the as-prepared sample. Optical image (A) and Raman spectroscopy (B) of monolayer WS₂ prepared by chemical vapor deposition (CVD). Raman spectroscopy are deconvoluted into four components with peak positions at 326.7 cm⁻¹, 351.4 cm⁻¹, 355.2 cm⁻¹, and 423.1 cm⁻¹, respectively. They can be attributed to the 2LA(M)-2E_{2g}¹(M), 2LA(M), E_{2g}¹(Γ), and A_{1g}(Γ), respectively, where E_{2g}¹(Γ), and A_{1g}(Γ) are the first order of the in-plane and out-of-plane modes, 2LA(M) and 2E_{2g}¹(M) are the second-order longitudinal acoustic phonon and second-order in-plane modes near the M point of the Brillouin zone [1-3]. (C) Atomic force microscope (AFM) image and (D) the corresponding height profile along the line in C.

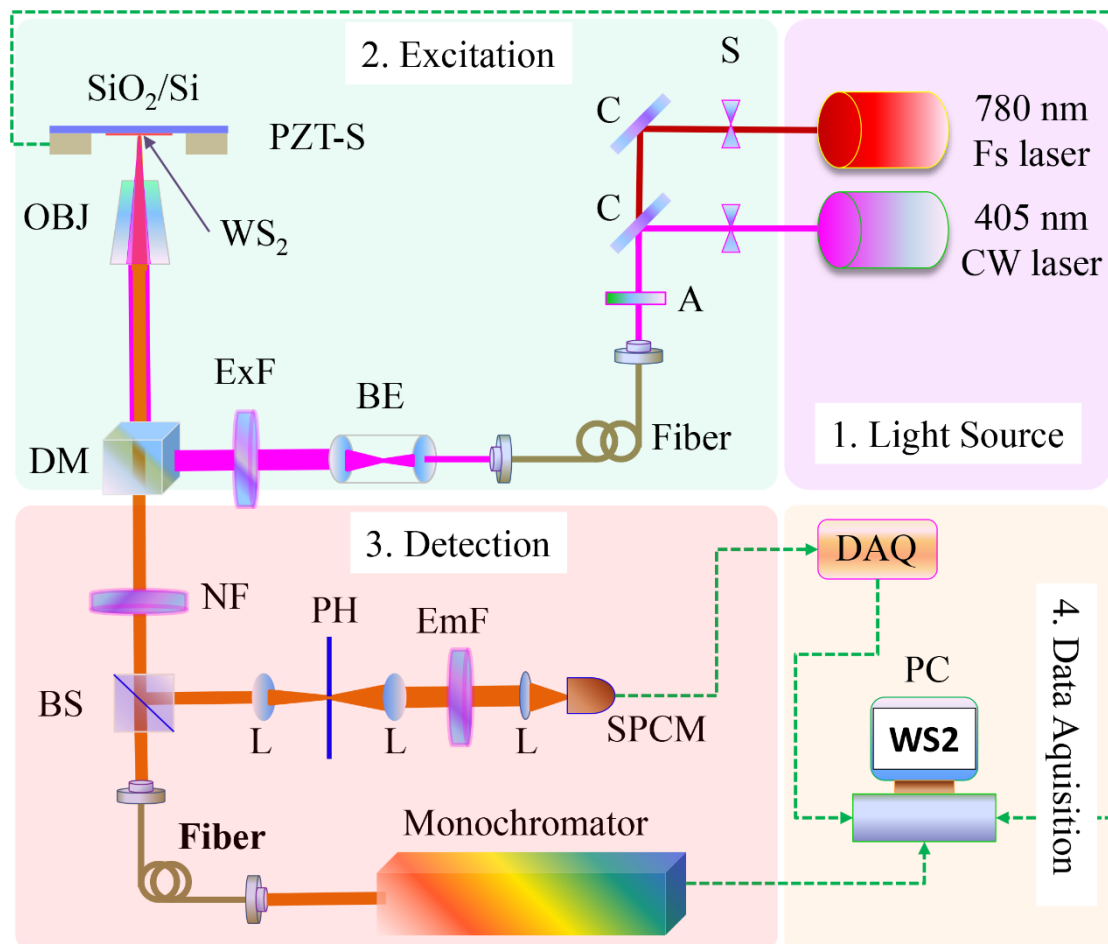


Fig. S2 Schematic diagram of the optical setup. S: shutter; C: beam combiner; A: attenuator; BE: beam expander; ExF: excitation filter; DM: dichroic mirror; OBJ: objective; PZT-S: piezo-electric translation nano-stage; NF: notch filter; BS: beam splitter; L: lens; PH: pinhole; EmF: emission filter; SPCM: single-photon counting modular; DAQ: data acquisition card; PC: personal computer.

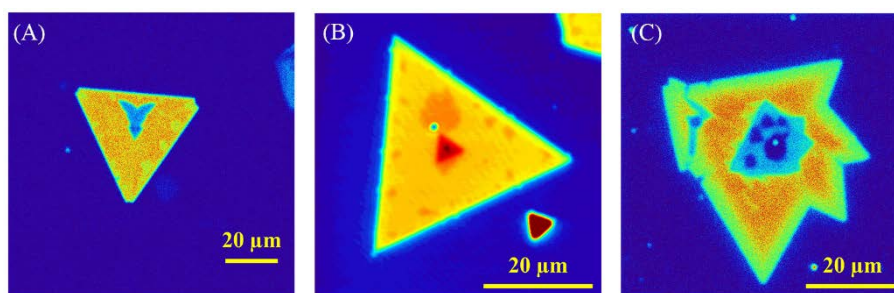


Fig. S3 PL imaging of the prepared WS₂. The inhomogeneous PL intensity indicates the inhomogeneous quality of monolayer WS₂.

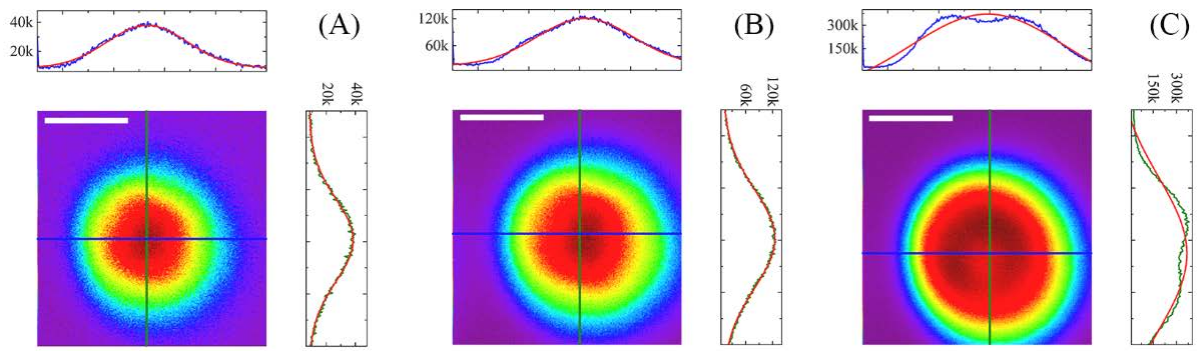


Fig. S4 Profiles of focused laser beam at the power density of 2.1, 7.0, and 15.0 MW/cm². The intensity profiles of the highlighted lines are all fitted by Gauss function. Scale bar: 1 μm.

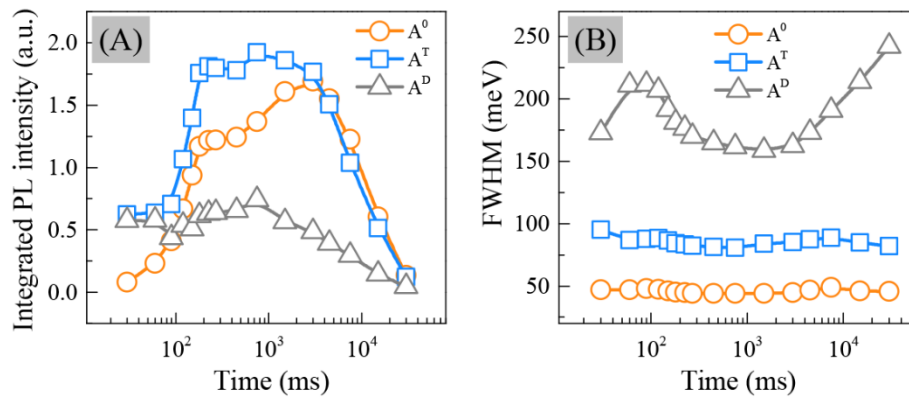


Fig. S5 Time evolution of integrated PL intensities (A) and full width at half maximum (FWHM) (B) of the exciton (A^0), trion (A^T), and defect-bound localized exciton (A^D) as a function of irradiation time (in log scale).

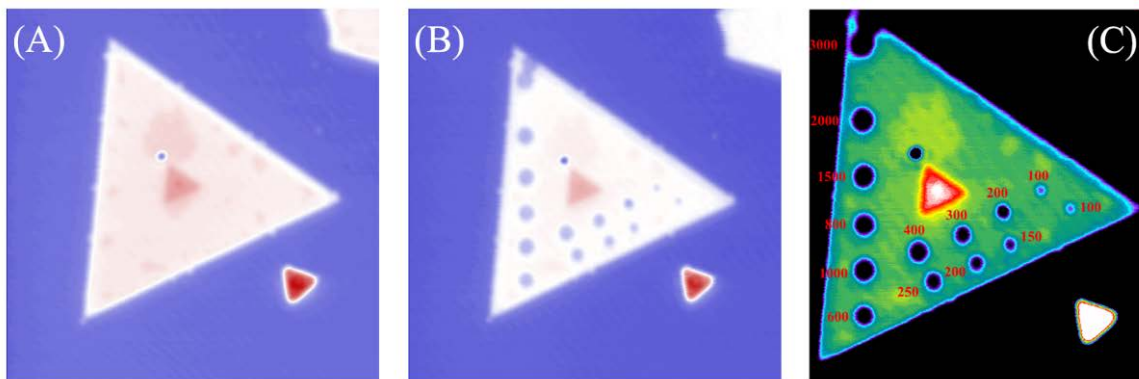


Fig. S6 PL image of the as-prepared (A) and post-engineered (B, C) monolayer WS₂ with different irradiation times (as labeled in C, the unit is ms) under vacuum condition (< 1 Pa). We can find that PL quenching can be observed under all conditions.

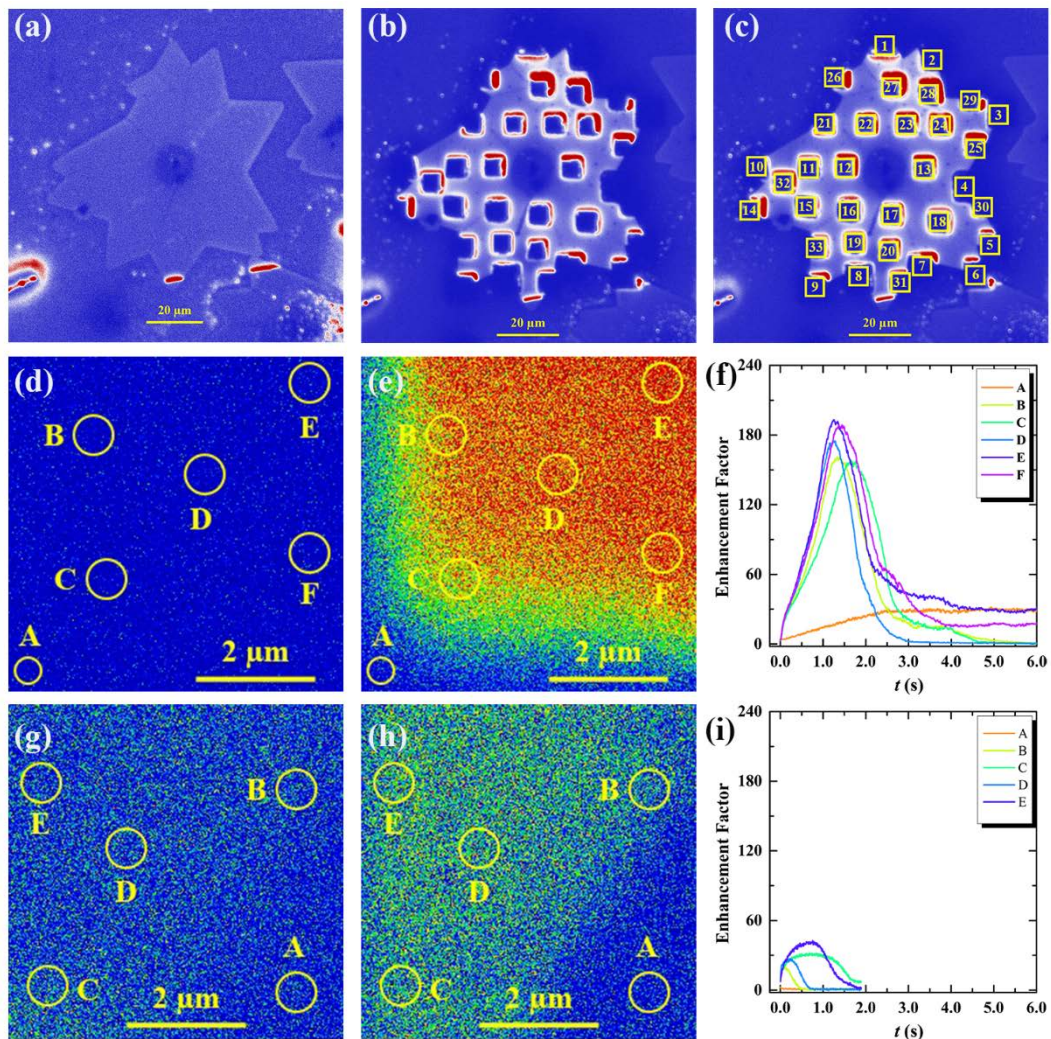


Fig. S7 Power-dependent PL enhancement factor trajectory. PL image of as-prepared (a) and post-engineered (b) monolayer WS₂ with different laser powers. The irradiation area was set as a 4 μm × 4 μm square. The laser power of each engineered area is listed in Table S1; the engineered sequence numbers have been labeled in (c). (d) PL image of the as-prepared sample (No. 11) and (e) the post-engineered area with the power density of 6.95 MW/cm² and time of 1.0 s, respectively. (f) PL enhancement factor trajectories of six selected areas, where A-E were used to gain the averaged enhancement factor. (g) PL image of the as-prepared sample (No. 31) and (e) the post-engineered area with the power density of 15.0 MW/cm² and time of 0.2 s, respectively. (f) PL enhancement factor trajectories of five selected areas, where A-D was used to gain the averaged enhancement factor.

Table S1 Irradiation powers of each marked area.

No.	Power (mW)	No.	Power (mW)
1	2.1	18	10.0
2	2.1	19	10.0
3	3.0	20	10.0
4	3.0	21	11.0

5	4.0	22	11.0
6	4.0	23	11.0
7	5.0	24	12.0
8	5.0	25	12.0
9	6.0	26	13.0
10	6.0	27	13.0
11	6.9	28	13.0
12	6.9	29	14.0
13	8.0	30	14.0
14	8.0	31	15.0
15	9.0	32	15.0
16	9.0	33	15.0
17	9.0		

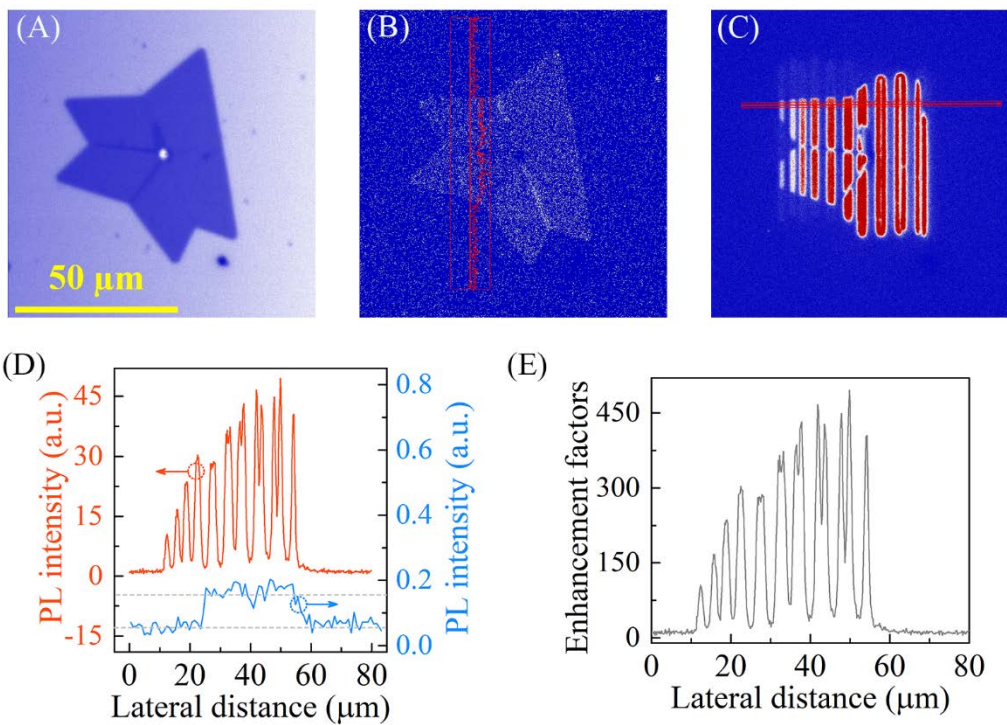


Fig. S8 (A) Reflection image and (B) PL image of as-prepared monolayer WS₂. (C) PL image of post-engineered monolayer WS₂ with the power of 8.3 MW/cm² and irradiation time of 1 s. We find that the grain boundary cannot be significantly enhanced. (D) PL intensities along the lines indicated in B and C. (E) Enhancement factor of the post-engineered area shown in C, calculated according to the PL intensity shown in Figure D. The maximum enhancement factor for this monolayer WS₂ can be up to more than 450.

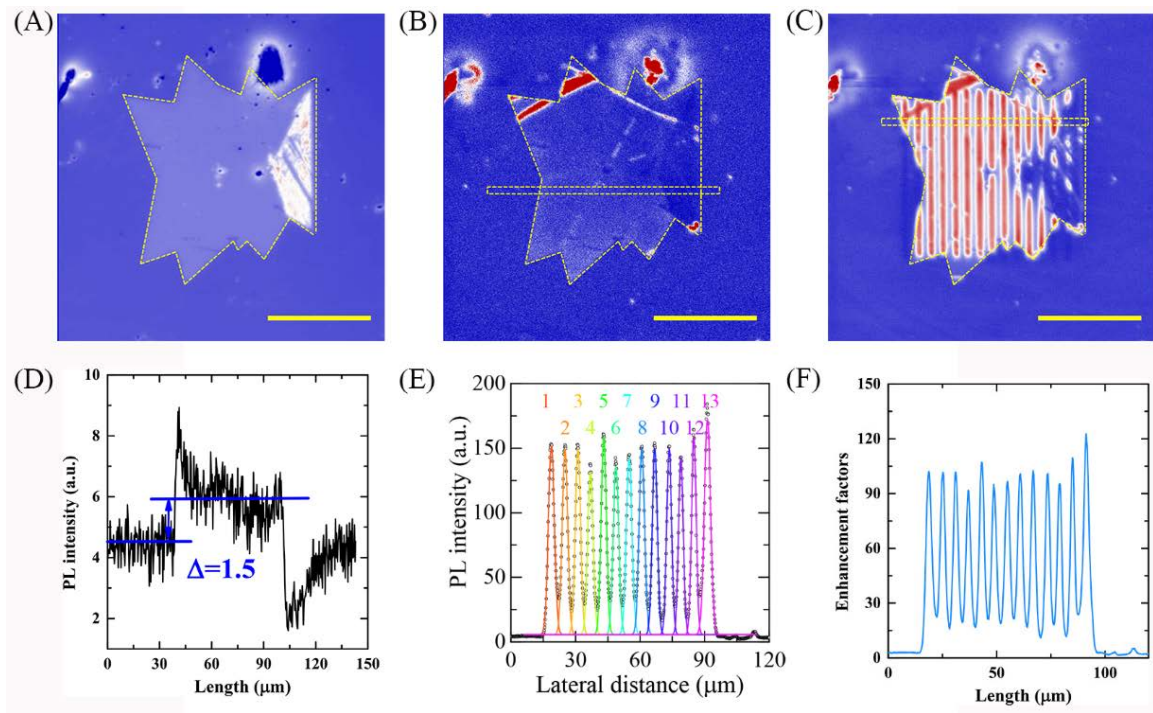


Fig. S9 Reflection image (A), PL image of as-prepared (B), and post-engineered (C) of monolayer WS₂. Scale bar: 50 μm. (D-E) PL intensity profiles along the B and C, respectively. The solid lines in E are the fitting curves by multi-Gauss functions. The fit results are listed in Table S2. (F) PL enhancement factor of the marked area shown in C.

Table S2 Fitted parameters of micro-grating.

No.	FWHM (μm)	Height (a.u.)
1	2.78	146
2	2.57	144
3	2.47	143
4	2.55	126
5	2.47	153
6	2.55	130
7	2.66	137
8	2.54	144
9	2.34	144
10	2.29	144
11	2.19	137
12	2.18	153
13	2.88	166

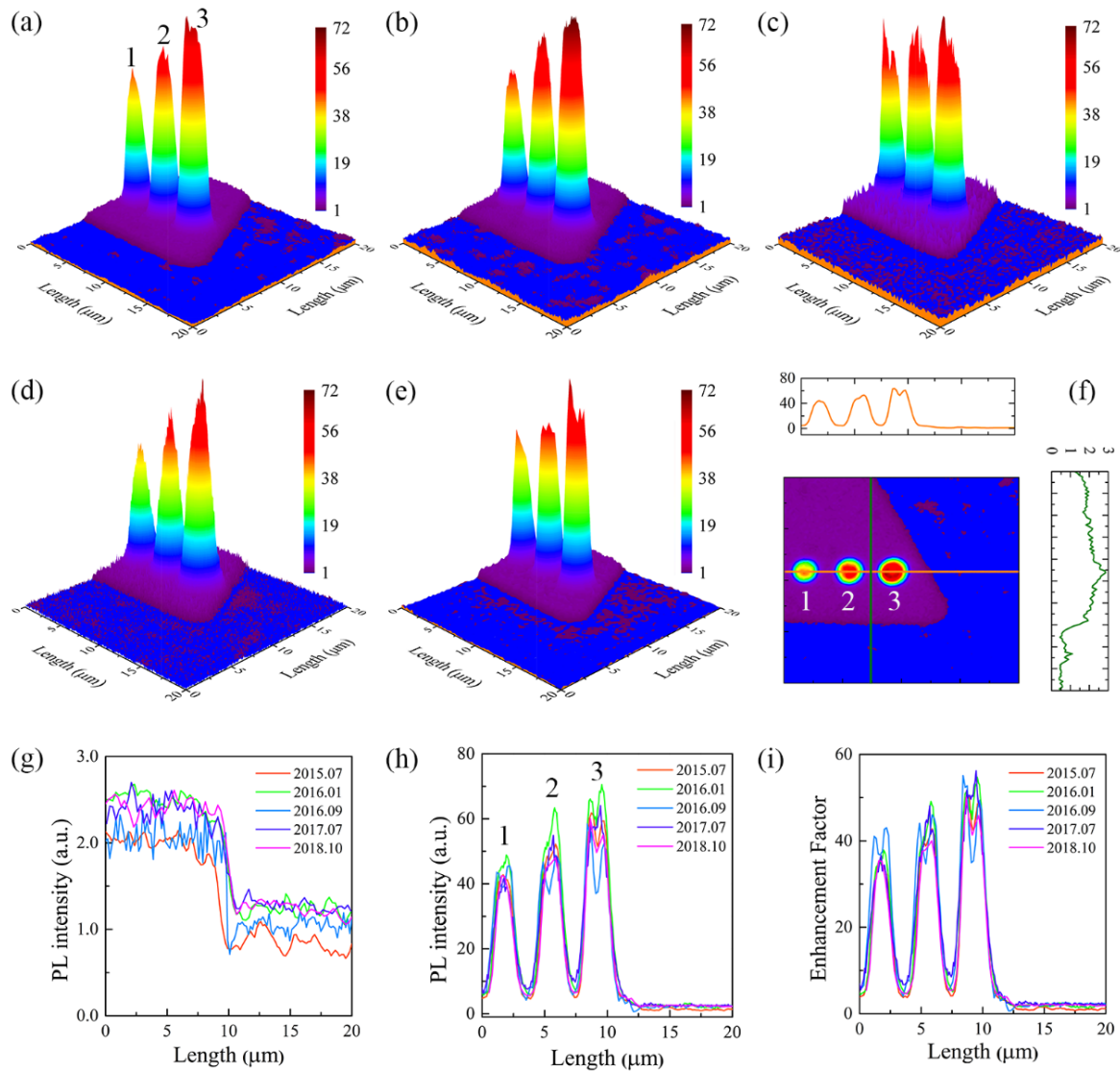


Fig. S10 Robust of the PL enhancement. Three-dimensional PL image of the engineered areas at (a) 2015.07 (first engineered), (b) 2016.01, (c) 2016.09, (d) 2017.07, and (e) 2018.10, respectively. The irradiation laser was femtosecond laser with the power density of 8.3 MW/cm^2 . The irradiation times for spots 1, 2, and 3 were 800 ms, 1000 ms, and 1200 ms, respectively. The excitation laser for PL image was 405 nm CW laser with the power density of 0.3 kW/cm^2 and the integrated time for each pixel of 0.01 s. The marked lines (f) and the corresponding PL intensity profiles of the as-prepared sample (g) and the post-engineered sample (h), respectively. (i) The calculated PL enhancement factors.

References

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